General purpose (Dual PNP Transistors)

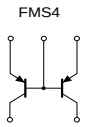
FMS4

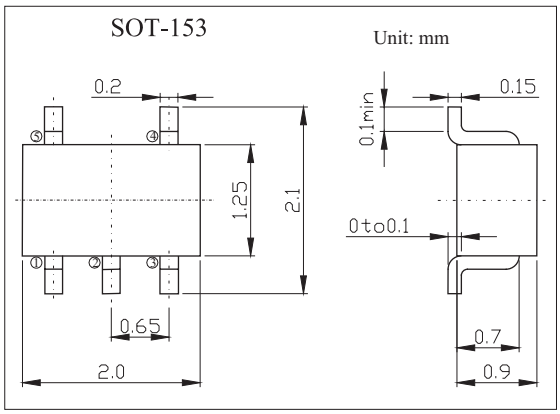
Features

High breakdown voltage

Power dissipation: P_C=300mW

Collector Curren: I_C=-50mA





Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current -Continuous	I_C	-50	mA
Collector Power Dissipation(TOTAL)	P_C	300	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C= -50μA, I_E=0	-120			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA I_B=0	-120			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E= -50 μA I_C=0	-5.0			V
Collector cutoff current	I_{CBO}	V_{CB}= -100 V , I_E=0			-0.5	μA
Collector cutoff current	I_{EBO}	V_{CE}= -4.0V , I_C=0			-0.5	μA
DC current gain	h_{FE}	V_{CE}= -60V, I_C= -2.0mA	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B= -1.0mA			-0.5	V
Transition frequency	f_T	V_{CE}= -12V, I_C= -2mA,f=100MHz		140		MHz

Marking

Marking	S4